

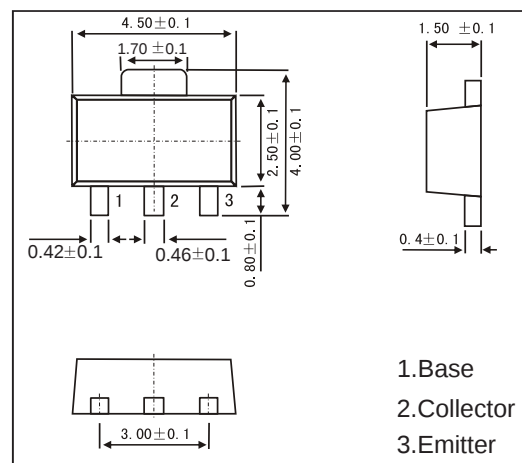
SOT-89 Plastic-Encapsulate Transistors

FEATURES

- Small Flat Package
- High Speed Switching Time
- Low Collector-emitter saturation voltage
- NPN Transistors

MECHANICAL DATA

- Case style:SOT-89molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CBO}	50	V
Collector - Emitter Voltage	V _{CEO}	50	
Emitter - Base Voltage	V _{EBO}	5	
Collector Current - Continuous	I _C	2	A
Collector Power Dissipation	P _C	500	mW
Thermal Resistance From Junction To Ambient	R _{θJA}	250	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CBO}	I _C = 100uA, I _E = 0	50			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = 1mA, I _B = 0	50			
Emitter - base breakdown voltage	V _{EBO}	I _E = 100uA, I _C = 0	5			
Collector-base cut-off current	I _{CBO}	V _{CB} = 50V, I _E = 0			0.1	uA
Emitter cut-off current	I _{EBO}	V _{EB} = 5V, I _C =0			0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =1A, I _B =50mA			0.5	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =1A, I _B =50mA			1.2	
DC current gain	h _{FE}	V _{CE} = 2V, I _C = 0.5A	70		240	
		V _{CE} = 2V, I _C = 2A	20			
Collector output capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f=1MHz		30		pF
Transition frequency	f _T	V _{CE} = 2V, I _C = 0.5A		120		MHz

RATINGS AND CHARACTERISTIC CURVES

